

a silicide layer formed on a surface of the semiconductor substrate excluding the first and second isolation regions;

91 a second diffusion region which is formed in a region isolated by the second isolation region and makes up a lateral bipolar transistor together with a well in the semiconductor substrate; and

a third diffusion region which is formed at a deeper position of the first diffusion region near the second isolation region and makes up a Zener diode by the PN junction together with the first diffusion region of the MOS transistor.

Page 8, lines 7-27 and Page 9, lines 1-6 delete current paragraph and insert therefor:

A further aspect of the present invention provides a method of fabricating a semiconductor device comprising the steps of:

forming a first isolation region which isolates a MOS transistor to be formed on a semiconductor substrate from other MOS transistors;

forming a second isolation region between the first isolation region and a region in which the MOS transistor is to be formed;

forming a P-type well and an N-type well in the semiconductor substrate;

92 forming a first diffusion region of the MOS transistor in a part of the P-type well and the N-type well near the boundary of the P-type and N-type wells of the semiconductor substrate;

forming a second diffusion region which make up a lateral bipolar transistor together with one of the P-type well and the N-type well of the semiconductor substrate in a region isolated by the second isolation region;

forming a third diffusion region which makes up a Zener diode by the PN junction together with the first diffusion region of the MOS transistor, between the second isolation

region and the first diffusion region and near a surface of the semiconductor substrate and;

92 and

forming a silicide layer on a surface of the semiconductor substrate excluding the first

Page 12, lines 22-27 and Page 13, lines 1-14, delete current paragraph and insert

therefor:

According to one embodiment of the present invention, there is provided a semiconductor device comprising:

a semiconductor substrate;

a MOS transistor which is formed on the semiconductor substrate and includes a first diffusion region;

a first isolation region which isolates the MOS transistor from other MOS transistors on the semiconductor substrate;

a second isolation region formed between the MOS transistor and the first isolation region;

a silicide layer formed on a surface of the semiconductor substrate excluding the first and second isolation regions;

a second diffusion region which is formed in a region isolated by the second isolation region and makes up a lateral bipolar transistor together with a well in the semiconductor substrate; and

a third diffusion region which is formed at a deeper position of the first diffusion region near the second isolation region and makes up a Zener diode by the PN junction

Page 20, lines 26-27 and Page 21, lines 1-25, delete current paragraph and insert therefor:

A further embodiment of the present invention provides a method of fabricating a semiconductor device comprising the steps of: